IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

REVOCATION OF POWER OF ATTORNEY, NEW POWER OF ATTORNEY BY ASSIGNEE AND CHANGE OF CORRESPONDENCE ADDRESS

Sir:

Assignee hereby revokes all powers of attorney previously granted with respect to the patent applications identified in Appendix A, and appoints the firm of Myers Bigel Sibley & Sajovec:

Customer No. 20792

as its attorney, with full power of substitution and revocation to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all communications as follows:

Customer No. 20792 Myers Bigel Sibley & Sajovec, P.A. P. O. Box 37428 Raleigh, North Carolina 27627 Telephone: (919) 854-1400 Facsimile: (919) 854-1401

Assignee hereby elects under 37 C.F.R. § 3.71 to prosecute the patent applications listed in Appendix A.

The undersigned Assignee hereby certifies that Samsung Electronics Co., Ltd. is the assignee of the entire right, title, and interest in the patent applications identified in Appendix A by virtue of a chain of title from the inventor(s) of the patent application identified to Hewlett-Packard Development Company, L.P. and then to the current assignee as shown in Appendix A.

The documents in the chain of title of the patent application identified above have been reviewed and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the Assignee.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Samsung Electronics Co., Ltd.

By: Jenny Jah Kong

Jeong-Taek Kong

Title: Senior Vice President of IP Team

Date: Aug. 23, 200)

APPENDIX A

In re:	Serial No.:	Filed	Title	Assignment Recorded: Reel:	Recl:	Frame:	Attv. Dkt. No.
Adelmann	10/621,632	07/17/03	Assisted Memory Device with Integrated Cache	HPDC 11/18/03	014138	1500	5649-2218
				Samsung 07/26/07	019613	0170	
Smith	10/743,662	12/22/03	MRAM with Controller	HPDC 12/22/03	014841	0615	5649-2219
				Samsung 07/26/07	119610	0239	0000000
Ретег	11/252,143	10/17/05	System and Method for Reading a Memory Cell	HPDC 01/27/04 Samsung 07/26/07	014930	0571	2049-2220
Anthony	11/021 268 12/23/04	12/23/04	Magnetic Memory Device and Methods for	HPC 02/10/03	013737	5860	5649-2221
and the same of			Making Same	HPDC 06/18/03	013776	8760	
				Samsung 07/26/07	019611	0807	
Jedwab	10/722,918	11/26/03	Magnetic Memory which Compares	HPDC 11/26/03	014756	0631	5649-2222
			Compressed Fault Maps	Samsung 07/26/07	019612	0632	
Sesek	10/700,203	11/03/03	Magnetic Memory	HPDC 06/22/04	014764	0438	5649-2223
				Samsung 07/26/07	019614	0135	
Pline	10/725,855	12/02/03	Data Storage System with Error Correction	HPDC 12/2/03	014757	0280	5649-2224
			Code and Replaceable Defective Memory	Samsung 07/26/07	019611	0690	
Spencer	11/203,755	8/15/05	Method of Packaging Magnetic Memory	HPC 03/04/03	013801	0643	5649-2225
				HPDC 09/30/03	014061	0492	
				Samsung 07/26/07	019611	0853	
25	10/698,501	10/31/03	Heating MRAM Cells to Ease State Switching	HPDC 02/09/04	014320	0883	5649-2226
				Samsung 07/26/07	019612	0754	
Stobbs	10/631,404	07/30/03	Magnetic Shielding for Magnetic Random	HPDC 09/11/03	013991	0927	5649-2227
			Access Memory	Samsung 07/26/07	019613	0864	
Taussig	10/914,255	08/09/04	Silver Island Anti-Fuse	HPDC 08/09/04	015678	0022	5649-2228
				Samsung 07/26/07	019613	0107	
Sharma	10/414,927 04/16/03	04/16/03	Optical Signal Transmission Transducer	HPC 06/09/03	013719	1010	5649-2230
				HPDC 09/30/03	014061	0492	
				Samsung 07/26/07	019611	0953	
Pemer	11/264,539	11/01/05	Controllably Connectable Strings of MRAM	HPDC 11/01/05	017180	0326	5649-2231
			Cells	Samsung 07/26/07	019612	6200	
Nickel	10/315,748	12/10/02	Thermally-Assisted Switching of Magnetic	HPC 06/22/01	011938	0028	5649-2232
			Memory Elements	HPDC 06/18/03	013776	0028	
I as	10/692 612	10/24/03	A Method of Makine a Magnetic Tunnel	HPDC 03/31/04	014478	0694	5649-2233
3_			Junction Device	Samsung 07/26/07	019612	0832	
Nauka	10/698,717	10/31/03	Data Storage Device Including Conductive	HPDC 10/31/03	014655	_	5649-2234
			Probe and Ferroelectric Storage Medium	Samsung 07/26/07	019612	\rightarrow	
Perner et al.	10/698,896	10/31/03	Multi-Sample Read Circuit Having Test Mode	HPDC 03/25/04	014461	0725	5649-2235
			of Operation	Samsung 07/26/07	019612	-	
Nickel	10/733,089	12/11/03	Using Sense Lines to Thermally Control the	HPDC 12/11/03	014817	0794	5649-2236
			State of an MKAM	Samsung 07/20/07	012013	-	

In re:	Serial No.:	Filed	Title	Assignment Recorded: Reel.	Reel	Frame:	Atty. Dkt. No.
Nickel	10/934,922	09/02/04	Thin Film Device and a Method of Formation	HPDC 09/02/04	015771	0250	5649-2237
Perner	10/934.243 09/03/04	09/03/04	Method and Apparatus for Multi-Plane MRAM	HPDC 09/03/04	015774	0570	5649-2238
				Samsung 07/26/07	019613	0064	
Zhang	10/721,574 11/25/03	11/25/03	Molecular Optoelectronic Memory Device	HPDC 03/31/04 Samsung 07/26/07	014478	0530 0206	5649-2239
Sharma	11/285,991	11/23/05	Multi-Layered Magnetic Memory Structures	HPDC 11/23/05	017281	5890	5649-2240
				Samsung 07/26/07	019613	0412	
Sharma	11/118,828	04/29/05	Process for Forming Magnetic Memory	HPDC 04/29/05	016527	0690	5649-2241
- Income	5015011 545 20011	1103/05	Multi-L avered Mannetic Memory Structures	HPDC 11/23/05	017281	0810	5649-2242
Silatina	Chairman	00/07	Comment of the commen	Samsung 07/26/07	019613	0465	
Sharma et al.	11/286.009 11/23/05	11/23/05	Multi-Layered Magnetic Memory Structures	HPDC 11/23/05	017281	0828	5649-2243
				Samsung 07/26/07	019613	0343	
Perner	11/266,861 11/03/05	11/03/05	Analog Preamplifier Calibration	HPDC 11/03/05	017195	0971	5649-2244
				Samsung 07/26/07	019611	0576	
Perner	11/267.705	11/03/05	Digital Current Source	HPDC 11/03/05	017226	6560	5649-2245
			•	Samsung 07/26/07	019612	0261	
Nickel	11/050.273	02/03/05	Method of Fabricating a Manganese Diffusion	HPDC 06/06/06	016306	0539	5649-2247
		_	Barricr	Samsung 07/26/07	019612	0337	
Eaton	10/661,448	09/11/03	Increased Magnetic Memory Array Sizes and	HPDC 12/03/03	014171	0302	5649-2248
			Operating Margins	Samsung 07/26/07	019613	0624	
Sharma	10/831,110 04/26/04	04/26/04	Data Input Device That Utilizes A Layer Of	HPDC 04/26/04	015226	0350	5649-2249
			Magnetic Particles To Store Non-Volatile Input	Samsung 07/26/07	019613	0531	
			Underlying MRAM Array (As Amended)				
Nickel	11/034,418	01/12/05	RF Field Heated Diodes for Providing	HPDC 01/12/05	016180	1560	5649-2250
			Thermally Assisted Switching of Magnetic	Samsung 07/26/07	410610	3	